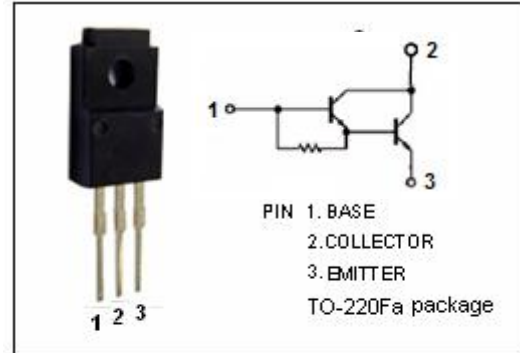


isc Silicon NPN Darlington Power Transistor
2SD1410
DESCRIPTION

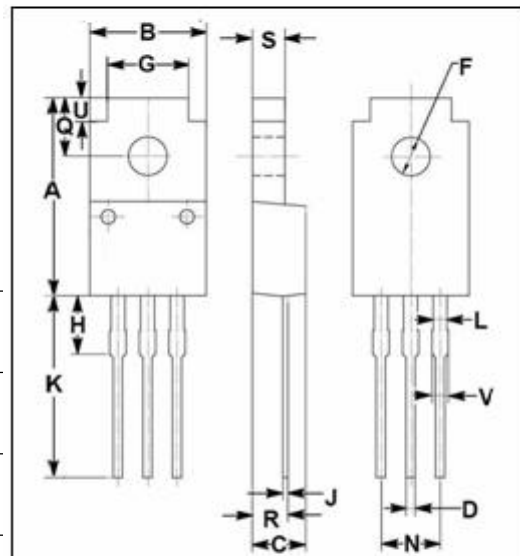
- Collector-Emitter Sustaining Voltage-
: $V_{CE(SUS)} = 250V(\text{Min})$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 2.0V(\text{Max}) @ I_C = 4A$
- High DC Current Gain
: $h_{FE} = 2000(\text{Min}) @ I_C = 2A, V_{CE} = 2V$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Igniter applications
- High voltage switching applications


ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	6	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2.0	W
	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	30	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

isc Silicon NPN Darlington Power Transistor
2SD1410
ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA ; L= 40mH	250			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 40mA			2.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4A; I _B = 40mA			2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 300V; I _E = 0			500	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0			500	μ A
h _{FE -1}	DC Current Gain	I _C = 2A ; V _{CE} = 2V	2000			
h _{FE -2}	DC Current Gain	I _C = 4A ; V _{CE} = 2V	200			
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} =1MHz		35		pF

Switching times

t _{on}	Turn-on Time	I _C = 4A , I _{B1} = I _{B2} = 40mA R _L = 25 Ω ; V _{CC} = 100V		1.0		μ s
t _{stg}	Storage Time			8.0		μ s
t _f	Fall Time			5.0		μ s

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